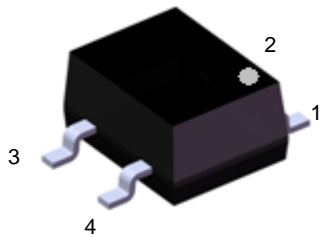


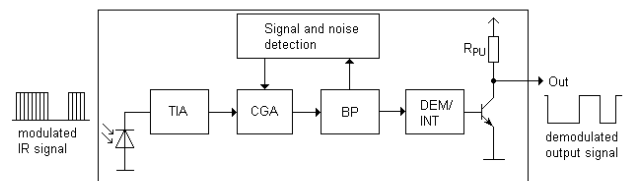
### Infrared Remote Control Receiver Module EAIRMKA1 & EAIRMKA2



#### Pin Configuration

1. GND
2. GND
3. OUT
4. Vcc

#### Block Diagram



#### Features

- High protection ability against EMI
- Available for various carrier frequencies
- Min burst length: 10 cycles
- Min gap length: 14 cycles
- Low operating voltage and low power consumption
- High immunity against ambient light
- Long reception range
- High sensitivity
- Pb free and RoHS compliant
- Compliance with EU REACH
- Compliance Halogen Free .(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm)

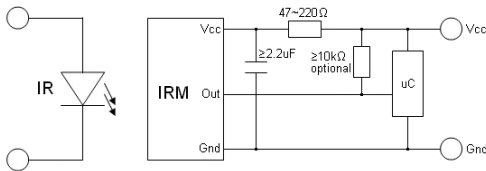
#### Descriptions

- The device is miniature SMD type infrared receiver that has been developed and designed by utilizing the latest IC technology.
- The PIN diode and preamplifier are assembled onto a lead frame and molded into a black epoxy package which operates as an IR filter. The demodulated output signal can directly be decoded by a microprocessor

#### Applications

- Light detecting portion of remote control
- AV instruments such as Audio, TV, VCR, CD, MD, etc
- Home appliances such as Air-conditioner, Fan, etc
- Other devices using IR remote control
- CATV set top boxes
- Multi-media Equipment

## Application Circuit



RC Filter should be connected closely between Vcc pin and GND pin.

## Parts Table

Model No.	Carrier Frequency
EAIRMKA1	36 kHz
EAIRMKA2	38 kHz

Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Rating	Unit
Supply Voltage	Vs	6	V
Operating Temperature	Topr	-20 ~ +80	°C
Storage Temperature	Tstg	-40 ~ +85	°C
Soldering Temperature <sup>*1</sup>	Tsol	260	°C

<sup>\*1</sup> 4mm from mold body less than 5 seconds

**Electro-Optical Characteristics (Ta=25°C and Vcc=3.0V)**

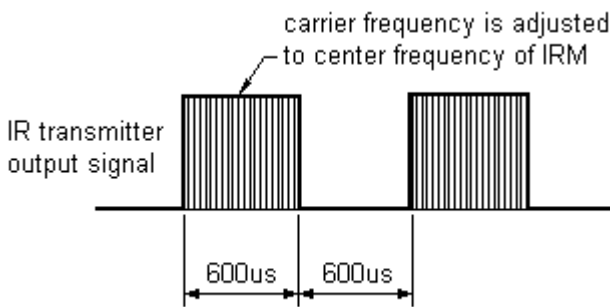
Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Condition
Current Consumption	I <sub>CC</sub>	-	0.4	0.6	mA	No signal input
Supply Voltage	V <sub>S</sub>	2.7	-	5.5	V	
Peak Wavelength	λ <sub>p</sub>	-	940	-	nm	
Reception Distance	L <sub>0</sub>	8	-	-	m	See chapter ,Test method'
	L <sub>45</sub>	5	-	-		
Half Angle (Horizontal)	Θ <sub>h</sub>	-	45	-	deg	
Half Angle (Vertical)	Θ <sub>v</sub>	-	45	-	deg	
High Level Pulse Width	T <sub>WH</sub>	450	-	750	μs	Test signal according to figure 1
Low Level Pulse Width	T <sub>WL</sub>	450	-	750	μs	
High Level Output Voltage	V <sub>H</sub>	V <sub>CC</sub> -0.4	-	-	V	
Low Level Output Voltage	V <sub>L</sub>	-	0.2	0.5	V	I <sub>SINK</sub> ≤ 2mA
Internal pull up resistor	R <sub>PU</sub>	85	100	115	kΩ	

**Test Method**

The specified electro-optical characteristic is satisfied under the following Conditions:

1. Measurement environment  
A place without extreme light reflected
2. External light  
Ordinary white fluorescent lamps (Light source temperature 2856°K,  $E_e \leq 10\text{Lux}$ ) without high frequency modulation
3. Standard transmitter  
The test transmitter is calibrated by using the circuit shown in figure 2. The radiation intensity of the transmitter is adjusted until  $V_o=400\text{mVp-p}$ . Both, the test transmitter and the photo diode, have a peak wavelength of 940nm. The photo diode for calibration is PD438B ( $\lambda_p=940\text{nm}$ ,  $V_r=5\text{V}$ ).
4. Measuring system According to the measuring system shown in Fig.-3

Fig.-1 Transmitter Wave Form



D.U.T output Pulse

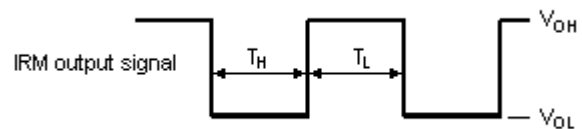


Fig.-2 Measuring Method

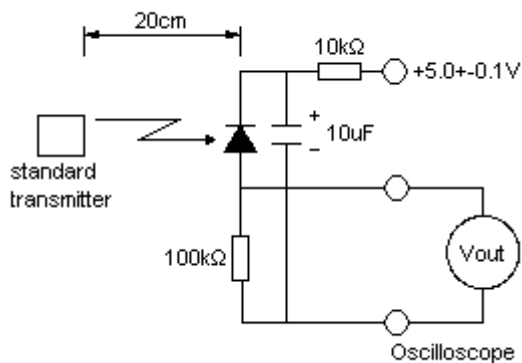
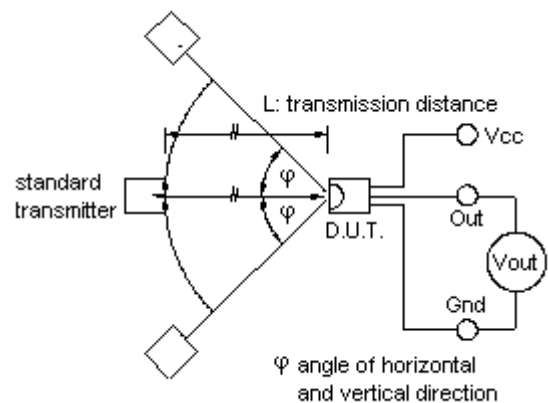
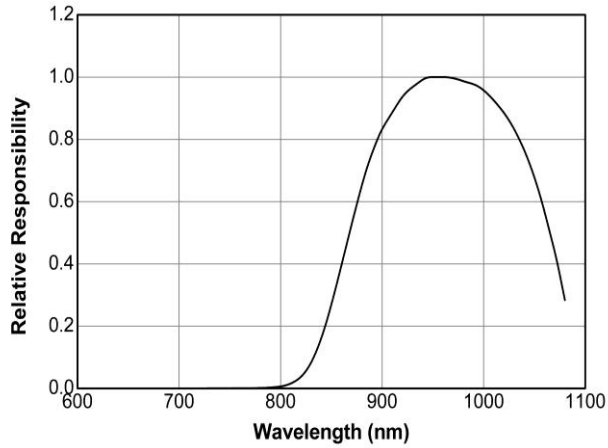


Fig.-3 Measuring System

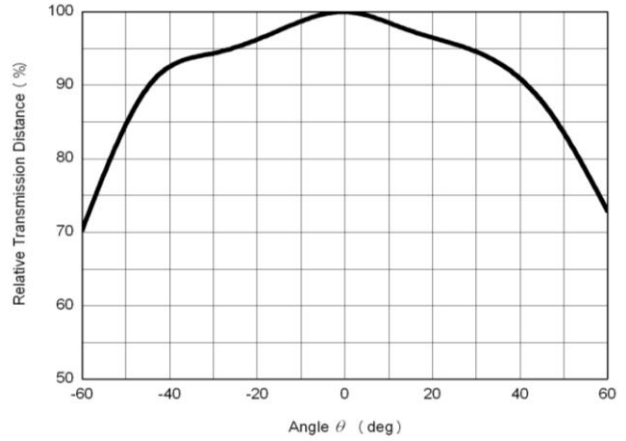


**Typical Performance Curves**

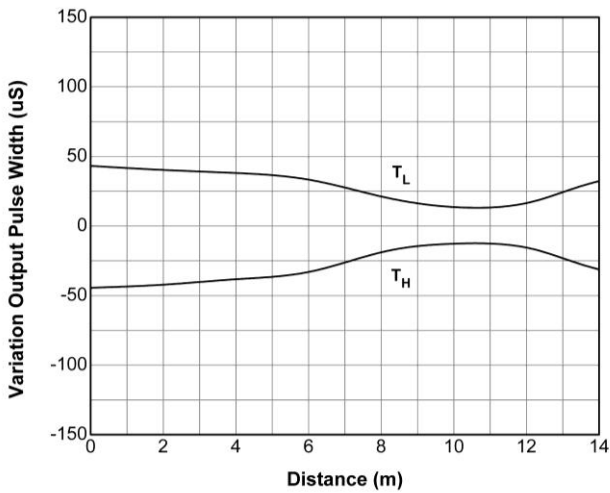
**Fig.4 Relative Responsibility vs. Wavelength**



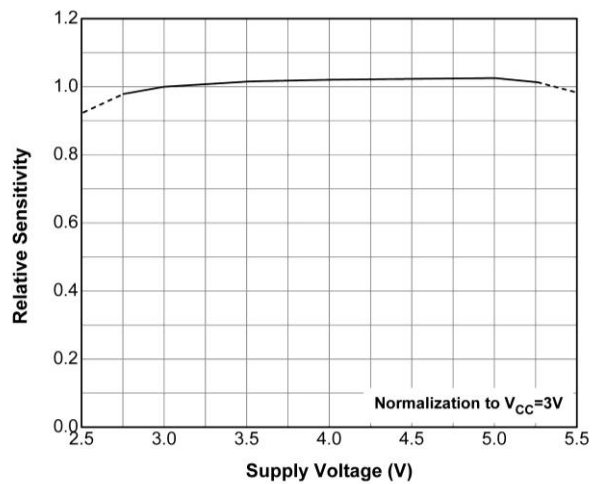
**Fig.-5 Relative Transmission Distance vs. Direction**



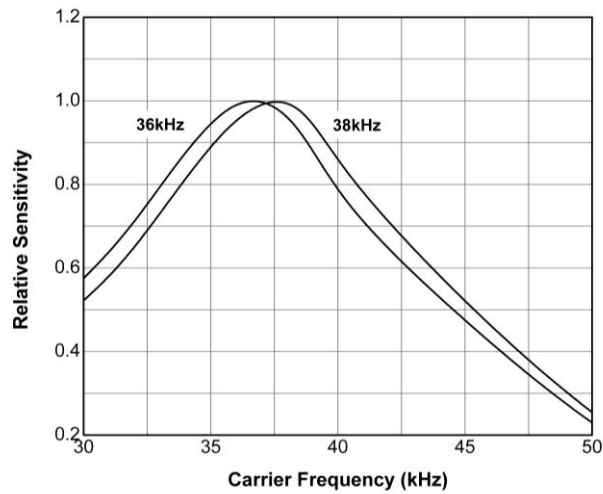
**Fig.6 Variation Output Pulse Width vs. Distance**



**Fig.7 Relative Sensitivity vs. Supply Voltage**

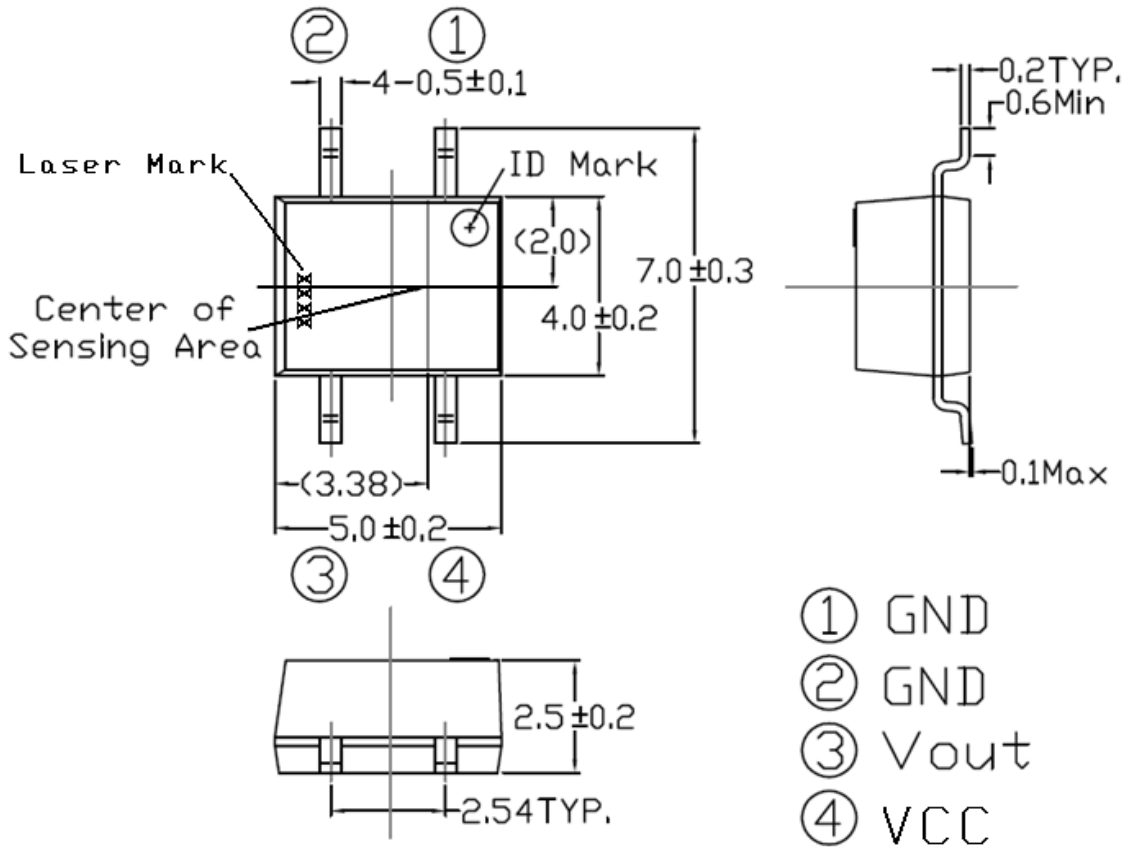


**Fig.8 Relative Sensitivity vs. Carrier Frequency**

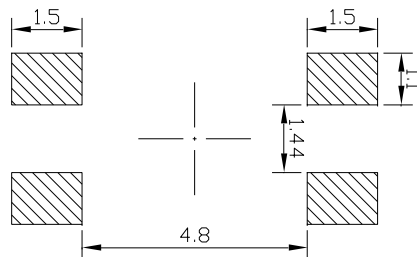


**Package Dimensions**

(Dimensions in mm)

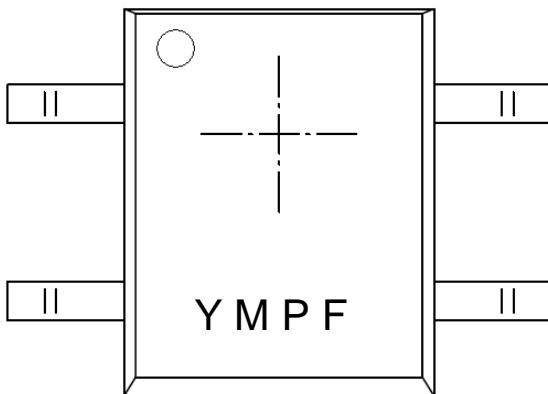


**Recommended pad layout for surface mount leadform**



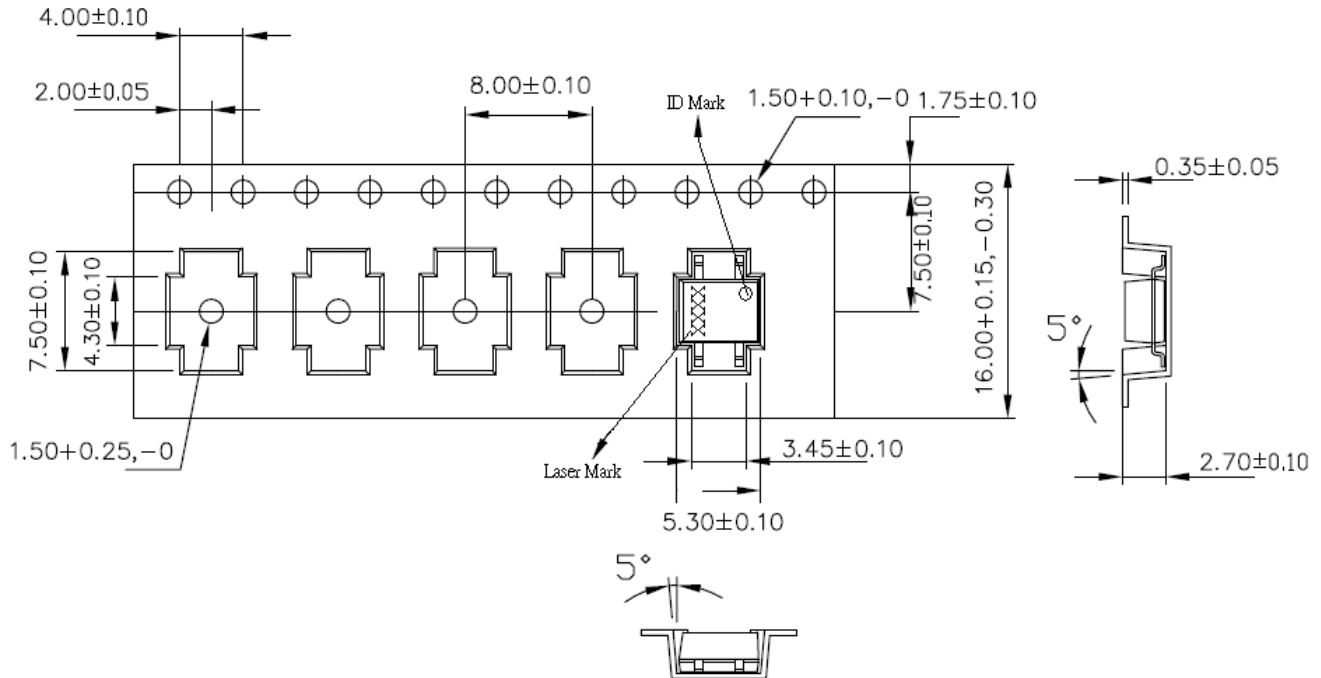
**Code information**

Protocol	Suitable	Protocol	Suitable
JVC	Yes	RCA	No
Matsushita	Yes	Sharp	Yes
Mitsubishi	No	Sony 12 Bit	Yes
NEC	Yes	Sony 15 Bit	No
RC5	Yes	Sony 20 Bit	No
RC6	Yes	Toshiba	Yes
RCMM	No	XMP-1	Yes
RCS-80	No	Continuous Code	No

**Device Marking****Notes**

- Y denotes Years code
- M denotes Month code
- P denotes Device number
- F denotes Carrier frequency (2: 36KHz, 4: 38KHz )

**Tape & Reel Packing Specifications**








**Packing Quantity**


1000 pcs / Reel

5 Reels / Carton



## Label format

	<b>EVERLIGHT</b>	<b>5</b>
CPN :		
P/N : XXXXXXXXX		
		<b>RoHS</b>
XXXXXXXXXX		
QTY : XXX	CAT : XX	
	HUE : XX	
LOT NO : XXXXXXXXXX	REF : XX	
		
Reference : XXXXXXXXX		
		

	<b>Caution</b> This bag contains <b>MOISTURE-SENSITIVE DEVICES</b>	<b>LEVEL</b> <input type="checkbox"/>
		<small>If blank, see adjacent bar code label</small>
1.	Calculated shelf life in sealed bag: 12 months at <40° C and <90% relative humidity (RH)	
2.	Peak package body temperature: _____°C <small>If blank, see adjacent bar code label</small>	
3.	After bag is opened, devices that will be subjected to reflow solder or other high temperature process must a) Mounted within: _____ hours of factory conditions <small>If blank, see adjacent bar code label</small> <30° C/60% RH, OR b) Stored at <10% RH	
4.	Devices require bake, before mounting, if: a) Humidity Indicator Card is >10% when read at 23 ± 5° C b) 3a or 3b not met	
5.	If baking is required, devices may be baked for 48 hours at 125 ± 5° C	
	<small>Note: If device containers cannot be subjected to high temperature or shorter bake times are desired, reference IPC/JEDEC J-STD-033 for bake procedure</small>	
	Bag Seal Date: _____ <small>If blank, see adjacent bar code label</small>	
	<small>Note: Level and body temperature defined by IPC/JEDEC J-STD-020</small>	

Moisture Classification-storage and used condition label

## Recommended method of storage

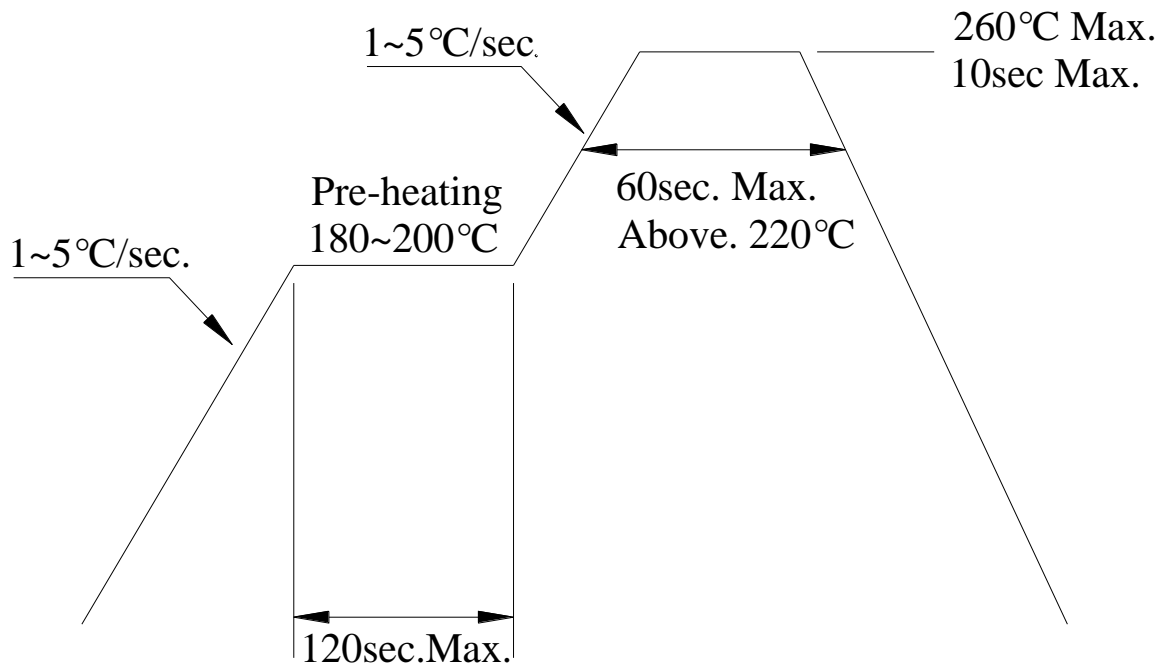
The following are general recommendations for moisture sensitive level (MSL) 4 storage and use:

1. Shelf life in sealed bag from the bag seal date: 12 months at < 40 °C and < 90% relative humidity (RH)
2. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must mounted within 72 hours of factory conditions < 30 °C/60%RH.
3. If the moisture absorbent material (silica gel) has faded away or the IRM has exceeded the storage time. Baking treatment is required, refer to IPC/JEDEC J-STD-033 for bake procedure or recommend the conditions: 60±5°C for 96 hours.

## ESD Precaution

Proper storage and handing procedures should be followed to prevent ESD damage to the devices especially when they are removed from the Anti-static bag. Electro-Static Sensitive Devices warning labels are on the packing.

## Solder Reflow Temperature Profile



### Note:

1. Reflow soldering should not be done more than two times.
2. When soldering, do not put stress on the IRM device during heating.
3. After soldering, do not warp the circuit board.

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2. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. Everlight Americas assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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